

## 0.75-Ω DUAL SPDT ANALOG SWITCH WITH INPUT LOGIC TRANSLATION

Check for Samples: [TS5A26542](#)

### FEATURES

- Specified Break-Before-Make Switching
- Low ON-State Resistance (0.75 Ω Max)
- Control Inputs Reference to  $V_{IO}$
- Low Charge Injection
- Excellent ON-State Resistance Matching
- Low Total Harmonic Distortion (THD)
- 2.25-V to 5.5-V Power Supply ( $V_+$ )
- 1.65-V to 1.95-V Logic Supply ( $V_{IO}$ )
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
  - 2000-V Human-Body Model (A114-B, Class II)
  - 1000-V Charged-Device Model (C101)
  - 300-V Machine Model (A115-A)
- COM Inputs
  - 8000-V Human-Body Model (A114-B, Class II)
  - ±15-kV Contact Discharge (IEC 61000-4-2)

### APPLICATIONS

- Cell Phones
- PDA's
- Portable Instrumentation

YZT PACKAGE<sup>(1)</sup>  
(BOTTOM VIEW)

	A	B	C	D
1	3	4	9	10
2	2	5	8	11
3	1	6	7	12

<sup>(1)</sup>The GND balls are internally connected.

	A	B	C	D
1	IN1	NO1	COM1	NC1
2	VIO	GND	GND	V+
3	IN2	NO2	COM2	NC2

### DESCRIPTION

The TS5A26542 is a dual single-pole double-throw (SPDT) analog switch that is designed to operate from 2.25 V to 5.5 V. The device offers a low ON-state resistance with an excellent channel-to-channel ON-state resistance matching, and the break-before-make feature to prevent signal distortion during the transferring of a signal from one path to the another. The device has excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications.

The TS5A26542 has a separate logic supply pin ( $V_{IO}$ ) that operates from 1.65 V to 1.95 V.  $V_{IO}$  powers the control circuitry, which allows the TS5A26542 to be controlled by 1.8-V signals.

**Table 1. ORDERING INFORMATION**

$T_A$	PACKAGE <sup>(1)</sup>		ORDERABLE PART NUMBER	TOP-SIDE MARKING <sup>(2)</sup>
–40°C to 85°C	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZT (Pb-free) 0.625-mm max height	Reel of 3000	TS5A26542YZTR	___ JN_

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at [www.ti.com](http://www.ti.com).

(2) YZT: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

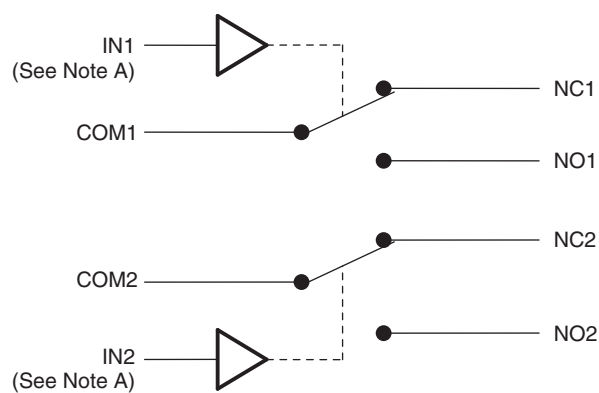
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**SUMMARY OF CHARACTERISTICS<sup>(1)</sup>**

Configuration	2:1 Multiplexer/Demultiplexer (2 × SPDT)
Number of channels	2
ON-state resistance ( $r_{on}$ )	0.75 $\Omega$ max
ON-state resistance match ( $\Delta r_{on}$ )	0.1 $\Omega$ max
ON-state resistance flatness ( $r_{on(flat)}$ )	0.1 $\Omega$ max
Turn-on/turn-off time ( $t_{ON}/t_{OFF}$ )	25 ns/20 ns
Charge injection ( $Q_C$ )	15 pC
Bandwidth (BW)	43 MHz
OFF isolation ( $O_{ISO}$ )	–63 dB at 1 MHz
Crosstalk ( $X_{TALK}$ )	–63 dB at 1 MHz
Total harmonic distortion (THD)	0.004%
Leakage current ( $I_{NO(OFF)}/I_{NC(OFF)}$ )	20 nA
Package option	12-pin WCSP

(1)  $V_+ = 5\text{ V}$ ,  $T_A = 25^\circ\text{C}$ **FUNCTION TABLE**

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
H	OFF	ON

**LOGIC DIAGRAM**A. IN1 and IN2 are control inputs referenced to  $V_{IO}$ .

## ABSOLUTE MAXIMUM RATINGS<sup>(1) (2)</sup>

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
$V_+$ $V_{IO}$	Supply voltage range <sup>(3)</sup>		–0.5	6.5	V
$V_{NC}$ $V_{NO}$ $V_{COM}$	Analog voltage range <sup>(3) (4) (5)</sup>		–0.5	$V_+ + 0.5$	V
$I_{I/O}$	Analog port diode current	$V_{NO}, V_{NC}, V_{COM} < 0$ or $V_{NO}, V_{NC}, V_{COM} > V_+$	–50	50	mA
$I_{NC}$ $I_{NO}$ $I_{COM}$	ON-state switch current	$V_{NO}, V_{NC}, V_{COM} = 0$ to $V_+$	–450	450	mA
	ON-state peak switch current <sup>(6)</sup>		–700	700	
$V_I$	Digital input voltage range <sup>(3) (4)</sup>		–0.5	6.5	V
$I_{IK}$	Digital input clamp current	$V_I < 0$	–50		mA
$I_+$ $I_{GND}$	Continuous current through $V_+$ or GND		–100	100	mA
$\theta_{JA}$	Package thermal impedance <sup>(7)</sup>			102	°C/W
$T_{stg}$	Storage temperature range		–65	150	°C

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) This value is limited to 5.5 V maximum.
- (6) Pulse at 1-ms duration <10% duty cycle
- (7) The package thermal impedance is calculated in accordance with JESD 51-7.

**ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY<sup>(1)</sup>**
 $V_+ = 4.5\text{ V to }5.5\text{ V}$ ,  $V_{IO} = 1.65\text{ V to }1.95\text{ V}$ ,  $T_A = -40^\circ\text{C to }85^\circ\text{C}$  (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T <sub>A</sub>	V <sub>+</sub>	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V <sub>COM</sub> , V <sub>NO</sub>					0		V <sub>+</sub>	V
ON-state resistance	r <sub>on</sub>	V <sub>NO</sub> or V <sub>NC</sub> = 2.5 V, I <sub>COM</sub> = −100 mA,	Switch ON, See <a href="#">Figure 14</a>	25°C	4.5 V	0.5		0.75	Ω
				Full		0.8			
ON-state resistance match between channels	Δr <sub>on</sub>	V <sub>NO</sub> or V <sub>NC</sub> = 2.5 V, I <sub>COM</sub> = −100 mA,	Switch ON, See <a href="#">Figure 14</a>	25°C	4.5 V	0.05		0.1	Ω
				Full		0.1			
ON-state resistance flatness	r <sub>on(flat)</sub>	0 ≤ (V <sub>NO</sub> or V <sub>NC</sub> ) ≤ V <sub>+</sub> , I <sub>COM</sub> = −100 mA,	Switch ON, See <a href="#">Figure 14</a>	25°C	4.5 V	0.1		Ω	
				25°C		0.1			
		V <sub>NO</sub> or V <sub>NC</sub> = 1 V, 1.5 V, 2.5 V, I <sub>COM</sub> = −100 mA,	Switch ON, See <a href="#">Figure 14</a>	Full		0.25			
NO, NC OFF leakage current	I <sub>NO(OFF)</sub> , I <sub>NC (OFF)</sub>	V <sub>NO</sub> = 1 V, 4.5 V, V <sub>COM</sub> = 4.5 V, 1 V, V <sub>NC</sub> = Open, or V <sub>NC</sub> = 1 V, 4.5 V, V <sub>COM</sub> = 4.5 V, 1 V, V <sub>NO</sub> = Open,	Switch OFF, See <a href="#">Figure 15</a>	25°C	5.5 V	−20	2	20	nA
				Full		−100		100	
NC, NO ON leakage current	I <sub>NO(ON)</sub>	V <sub>NO</sub> = 1 V, 4.5 V, V <sub>NC</sub> and V <sub>COM</sub> = Open, or V <sub>NC</sub> = 1V, 4.5 V, V <sub>NO</sub> and V <sub>COM</sub> = Open,	Switch ON, See <a href="#">Figure 16</a>	25°C	5.5 V	−20	2	20	nA
				Full		−200		200	
COM ON leakage current	I <sub>COM(ON)</sub>	V <sub>COM</sub> = 1 V, V <sub>NO</sub> and V <sub>NC</sub> = Open, or V <sub>COM</sub> = 4.5 V, V <sub>NO</sub> and V <sub>NC</sub> = Open,	See <a href="#">Figure 16</a>	25°C	5.5 V	−20	2	20	nA
				Full		−200		200	
Digital Control Inputs (IN1, IN2) <sup>(2)</sup>									
Input logic high	V <sub>IH</sub>	V <sub>IO</sub> = 1.65 V to 1.95 V		Full		0.65 × V <sub>IO</sub>		V <sub>IO</sub>	V
Input logic low	V <sub>IL</sub>	V <sub>IO</sub> = 1.65 V to 1.95 V		Full		0		0.35 × V <sub>IO</sub>	V
Input leakage current	I <sub>IH</sub> , I <sub>IL</sub>	V <sub>I</sub> = V <sub>IO</sub> or 0		25°C	5.5 V	−2		2	nA
				Full		−20		20	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at  $V_{IO}$  or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

**ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY<sup>(1)</sup> (continued)**
 $V_+ = 4.5 \text{ V to } 5.5 \text{ V}$ ,  $V_{IO} = 1.65 \text{ V to } 1.95 \text{ V}$ ,  $T_A = -40^\circ\text{C to } 85^\circ\text{C}$  (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T <sub>A</sub>	V+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t <sub>ON</sub>	V <sub>COM</sub> = V <sub>+</sub> , R <sub>L</sub> = 50 Ω,	C <sub>L</sub> = 35 pF, See <a href="#">Figure 18</a>	25°C	5 V	1	12.5	25	ns
				Full	4.5 V			30	
Turn-off time	t <sub>OFF</sub>	V <sub>COM</sub> = V <sub>+</sub> , R <sub>L</sub> = 50 Ω,	C <sub>L</sub> = 35 pF, See <a href="#">Figure 18</a>	25°C	5 V	1	9.5	20	ns
				Full	4.5 V			25	
Break-before-make time	t <sub>BBM</sub>	V <sub>NC</sub> = V <sub>NO</sub> = V <sub>+</sub> /2, R <sub>L</sub> = 50 Ω,	C <sub>L</sub> = 35 pF, See <a href="#">Figure 19</a>	25°C	5 V	1	5	10	ns
				Full	4.5 V	1		12	
Charge injection	Q <sub>C</sub>	V <sub>GEN</sub> = 0, R <sub>GEN</sub> = 0,	C <sub>L</sub> = 1 nF, See <a href="#">Figure 23</a>	25°C	5 V		15		pC
NO OFF capacitance	C <sub>NO(OFF)</sub>	V <sub>NO</sub> = V <sub>+</sub> or GND, Switch OFF,	See <a href="#">Figure 17</a>	25°C	5 V		37		pF
NC, NO ON capacitance	C <sub>NC(ON)</sub> , C <sub>NO(ON)</sub>	V <sub>NC</sub> or V <sub>NO</sub> = V <sub>+</sub> or GND, Switch ON,	See <a href="#">Figure 17</a>	25°C	5 V		130		pF
COM ON capacitance	C <sub>COM(ON)</sub>	V <sub>COM</sub> = V <sub>+</sub> or GND, Switch ON,	See <a href="#">Figure 17</a>	25°C	5 V		130		pF
Digital input capacitance	C <sub>I</sub>	V <sub>I</sub> = V <sub>IO</sub> or GND,	See <a href="#">Figure 17</a>	25°C	5 V		6.5		pF
Bandwidth	BW	R <sub>L</sub> = 50 Ω, Switch ON,	See <a href="#">Figure 20</a>	25°C	5 V		43		MHz
OFF isolation	O <sub>ISO</sub>	R <sub>L</sub> = 50 Ω, f = 1 MHz,	See <a href="#">Figure 21</a>	25°C	5 V		−63		dB
Crosstalk	X <sub>TALK</sub>	R <sub>L</sub> = 50 Ω, f = 1 MHz,	See <a href="#">Figure 22</a>	25°C	5 V		−63		dB
Total harmonic distortion	THD	R <sub>L</sub> = 600 Ω, C <sub>L</sub> = 50 pF,	f = 20 Hz to 20 kHz, See <a href="#">Figure 24</a>	25°C	5 V		0.004		%
Supply									
Positive supply current	I <sub>+</sub>	V <sub>I</sub> = V <sub>IO</sub> or GND		25°C	5.5 V		5.5	100	nA
				Full				750	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

## Electrical Characteristics for 3.3-V Supply<sup>(1)</sup>

$V_+ = 3\text{ V}$  to  $3.6\text{ V}$ ,  $V_{IO} = 1.65\text{ V}$  to  $1.95\text{ V}$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$  (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	$T_A$	$V_+$	MIN	TYP	MAX	UNIT
<b>Analog Switch</b>								
Analog signal range	$V_{COM}, V_{NO}$				0		$V_+$	V
ON-state resistance	$r_{on}$	$V_{NO}$ or $V_{NC} = 2\text{ V}$ , $I_{COM} = -100\text{ mA}$ , Switch ON, See <a href="#">Figure 14</a>	25°C Full	3 V	0.75		0.9 1.2	$\Omega$
ON-state resistance match between channels	$\Delta r_{on}$	$V_{NO}$ or $V_{NC} = 2\text{ V}$ , $0.8\text{ V}$ , $I_{COM} = -100\text{ mA}$ , Switch ON, See <a href="#">Figure 14</a>	25°C Full	3 V	0.1		0.15 0.15	$\Omega$
ON-state resistance flatness	$r_{on(flat)}$	$0 \leq (V_{NO} \text{ or } V_{NC}) \leq V_+$ , $I_{COM} = -100\text{ mA}$ , Switch ON, See <a href="#">Figure 14</a>	25°C Full	3 V	0.2 0.1		0.3 0.3	$\Omega$
NO, NC OFF leakage current	$I_{NO(OFF)}, I_{NC(OFF)}$	$V_{NO} = 1\text{ V}$ , $3\text{ V}$ , $V_{COM} = 3\text{ V}$ , $1\text{ V}$ , $V_{NC} = \text{Open}$ , or $V_{NC} = 1\text{ V}$ , $3\text{ V}$ , $V_{COM} = 3\text{ V}$ , $1\text{ V}$ , $V_{NO} = \text{Open}$ , Switch OFF, See <a href="#">Figure 15</a>	25°C Full	3.6 V	-20 -50	2	20 50	nA
NC, NO ON leakage current	$I_{NO(ON)}$	$V_{NO} = 1\text{ V}$ , $3\text{ V}$ , $V_{NC}$ and $V_{COM} = \text{Open}$ , or $V_{NC} = 1\text{ V}$ , $3\text{ V}$ , $V_{NO}$ and $V_{COM} = \text{Open}$ , Switch ON, See <a href="#">Figure 16</a>	25°C Full	3.6 V	-10 30	2	10 30	nA
COM ON leakage current	$I_{COM(ON)}$	$V_{COM} = 1\text{ V}$ , $V_{NO}$ and $V_{NC} = \text{Open}$ , or $V_{COM} = 3\text{ V}$ , $V_{NO}$ and $V_{NC} = \text{Open}$ , See <a href="#">Figure 16</a>	25°C Full	3.6 V	-10 -30	2	10 30	nA
<b>Digital Control Inputs (IN1, IN2)<sup>(2)</sup></b>								
Input logic high	$V_{IH}$	$V_{IO} = 1.65\text{ V}$ to $1.95\text{ V}$	Full		$0.65 \times V_{IO}$		$V_{IO}$	V
Input logic low	$V_{IL}$	$V_{IO} = 1.65\text{ V}$ to $1.95\text{ V}$	Full		0		$0.35 \times V_{IO}$	V
Input leakage current	$I_{IH}, I_{IL}$	$V_I = V_{IO}$ or 0	25°C Full	3.6 V	-2 -20		2 20	nA

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at  $V_{IO}$  or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

**ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY<sup>(1)</sup> (continued)**
 $V_+ = 3\text{ V to }3.6\text{ V}$ ,  $V_{IO} = 1.65\text{ V to }1.95\text{ V}$ ,  $T_A = -40^\circ\text{C to }85^\circ\text{C}$  (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T <sub>A</sub>	V <sub>+</sub>	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t <sub>ON</sub>	V <sub>COM</sub> = V <sub>+</sub> , R <sub>L</sub> = 50 Ω,	C <sub>L</sub> = 35 pF, See <a href="#">Figure 18</a>	25°C	3.3 V	5	15	30	ns
				Full	3 V	3		35	
Turn-off time	t <sub>OFF</sub>	V <sub>COM</sub> = V <sub>+</sub> , R <sub>L</sub> = 50 Ω,	C <sub>L</sub> = 35 pF, See <a href="#">Figure 18</a>	25°C	3.3 V	1	9	20	ns
				Full	3 V	1		25	
Break-before-make time	t <sub>BBM</sub>	V <sub>NC</sub> = V <sub>NO</sub> = V <sub>+</sub> /2, R <sub>L</sub> = 50 Ω,	C <sub>L</sub> = 35 pF, See <a href="#">Figure 19</a>	25°C	3.3 V	1	8	13	ns
				Full	3 V	1		15	
Charge injection	Q <sub>C</sub>	V <sub>GEN</sub> = 0, R <sub>GEN</sub> = 0,	C <sub>L</sub> = 1 nF, See <a href="#">Figure 23</a>	25°C	3.3 V		6.5		pC
NO OFF capacitance	C <sub>NO(OFF)</sub>	V <sub>NO</sub> = V <sub>+</sub> or GND, Switch OFF,	See <a href="#">Figure 17</a>	25°C	3.3 V		38		pF
NC, NO ON capacitance	C <sub>NC(ON)</sub> , C <sub>NO(ON)</sub>	V <sub>NC</sub> or V <sub>NO</sub> = V <sub>+</sub> or GND, Switch ON,	See <a href="#">Figure 17</a>	25°C	3.3 V		133		pF
COM ON capacitance	C <sub>COM(ON)</sub>	V <sub>COM</sub> = V <sub>+</sub> or GND, Switch ON,	See <a href="#">Figure 17</a>	25°C	3.3 V		133		pF
Digital input capacitance	C <sub>I</sub>	V <sub>I</sub> = V <sub>IO</sub> or GND,	See <a href="#">Figure 17</a>	25°C	3.3 V		6.5		pF
Bandwidth	BW	R <sub>L</sub> = 50 Ω, Switch ON,	See <a href="#">Figure 20</a>	25°C	3.3 V		42		MHz
OFF isolation	O <sub>ISO</sub>	R <sub>L</sub> = 50 Ω, f = 1 MHz,	See <a href="#">Figure 21</a>	25°C	3.3 V		−63		dB
Crosstalk	X <sub>TALK</sub>	R <sub>L</sub> = 50 Ω, f = 1 MHz,	See <a href="#">Figure 22</a>	25°C	3.3 V		−63		dB
Total harmonic distortion	THD	R <sub>L</sub> = 600 Ω, C <sub>L</sub> = 50 pF,	f = 20 Hz to 20 kHz, See <a href="#">Figure 24</a>	25°C	3.3 V		0.004		%
Supply									
Positive supply current	I <sub>+</sub>	V <sub>I</sub> = V <sub>IO</sub> or GND	25°C	3.6 V		10	50	nA	
			Full				300		

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

**ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY<sup>(1)</sup>**
 $V_+ = 2.25\text{ V to }2.75\text{ V}$ ,  $V_{IO} = 1.65\text{ V to }1.95\text{ V}$ ,  $T_A = -40^\circ\text{C to }85^\circ\text{C}$  (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T <sub>A</sub>	V <sub>+</sub>	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V <sub>COM</sub> , V <sub>NO</sub>					0		V <sub>+</sub>	V
ON-state resistance	r <sub>on</sub>	V <sub>NO</sub> or V <sub>NC</sub> = 1.8 V, I <sub>COM</sub> = −100 mA,	Switch ON, See <a href="#">Figure 14</a>	25°C Full	2.25 V	1		1.3 1.6	Ω
ON-state resistance match between channels	Δr <sub>on</sub>	V <sub>NO</sub> or V <sub>NC</sub> = 1.8 V, 0.8 V, I <sub>COM</sub> = −100 mA,	Switch ON, See <a href="#">Figure 14</a>	25°C Full	2.25 V	0.15		0.2 0.2	Ω
ON-state resistance flatness	r <sub>on(flat)</sub>	0 ≤ (V <sub>NO</sub> or V <sub>NC</sub> ) ≤ V <sub>+</sub> , I <sub>COM</sub> = −100 mA,	Switch ON, See <a href="#">Figure 14</a>	25°C	2.25 V	0.5			Ω
		V <sub>NO</sub> or V <sub>NC</sub> = 0.8 V, 1 V, 1.8 V, I <sub>COM</sub> = −100 mA,	Switch ON, See <a href="#">Figure 14</a>	25°C Full		0.25		0.5 0.6	
NO, NC OFF leakage current	I <sub>NO(OFF)</sub> , I <sub>NC (OFF)</sub>	V <sub>NO</sub> = 0.5 V, 2.2 V, V <sub>COM</sub> = 2.2 V, 0.5 V, V <sub>NC</sub> = Open, or V <sub>NC</sub> = 0.5 V, 2.2 V, V <sub>COM</sub> = 2.2 V, 0.5 V, V <sub>NO</sub> = Open,	Switch OFF, See <a href="#">Figure 15</a>	25°C Full	2.75 V	−20 −50	2	20 50	nA
NC, NO ON leakage current	I <sub>NO(ON)</sub>	V <sub>NO</sub> = 0.5 V, 2.2 V, V <sub>NC</sub> and V <sub>COM</sub> = Open, or V <sub>NC</sub> = 0.5 V, 2.2 V, V <sub>NO</sub> and V <sub>COM</sub> = Open,	Switch ON, See <a href="#">Figure 16</a>	25°C Full	2.75 V	−10 −20	2	10 20	nA
COM ON leakage current	I <sub>COM(ON)</sub>	V <sub>COM</sub> = 0.5 V, V <sub>NO</sub> and V <sub>NC</sub> = Open, or V <sub>COM</sub> = 2.2 V, V <sub>NO</sub> and V <sub>NC</sub> = Open,	Switch ON, See <a href="#">Figure 16</a>	25°C Full	2.75 V	−10 −50	2	10 50	nA
Digital Control Inputs (IN1, IN2) <sup>(2)</sup>									
Input logic high	V <sub>IH</sub>	V <sub>IO</sub> = 1.65 V to 1.95 V		Full		0.65 × V <sub>IO</sub>		V <sub>IO</sub>	V
Input logic low	V <sub>IL</sub>	V <sub>IO</sub> = 1.65 V to 1.95 V		Full		0		0.35 × V <sub>IO</sub>	V
Input leakage current	I <sub>IH</sub> , I <sub>IL</sub>	V <sub>I</sub> = V <sub>IO</sub> or 0		25°C Full	2.75 V	−2 −20		2 20	nA

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at  $V_{IO}$  or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

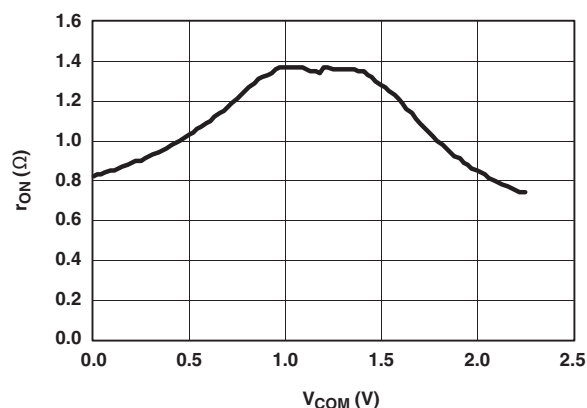
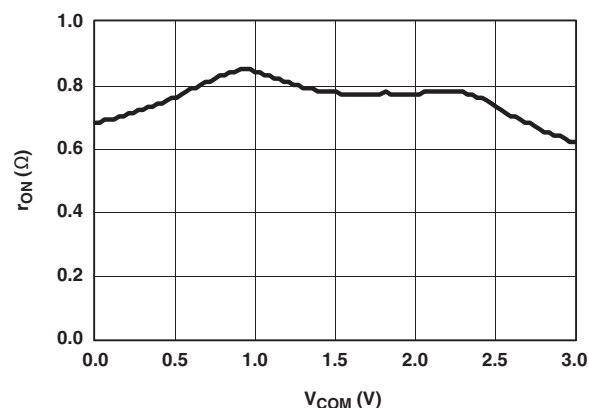
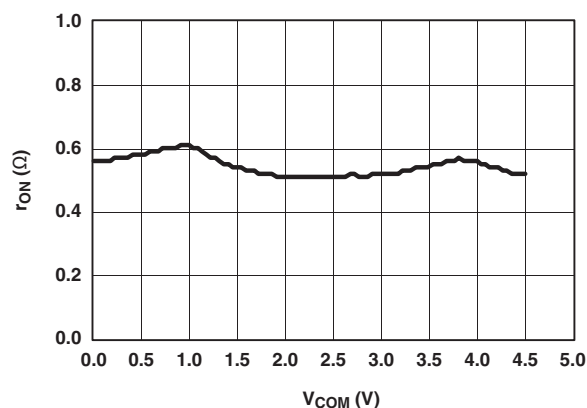
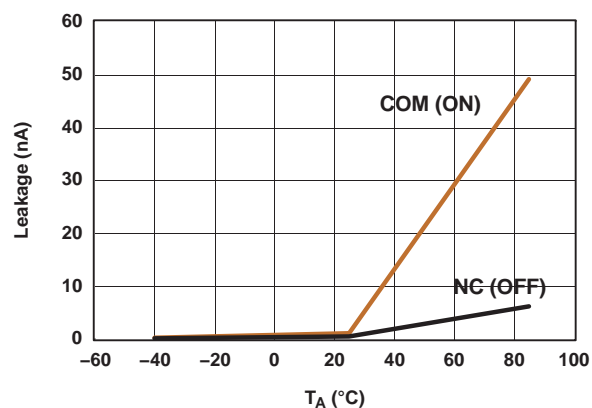
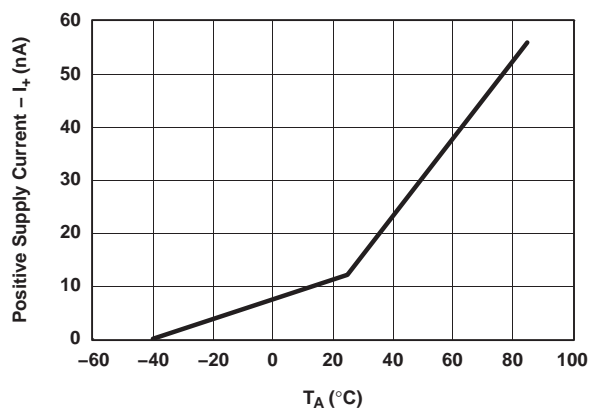
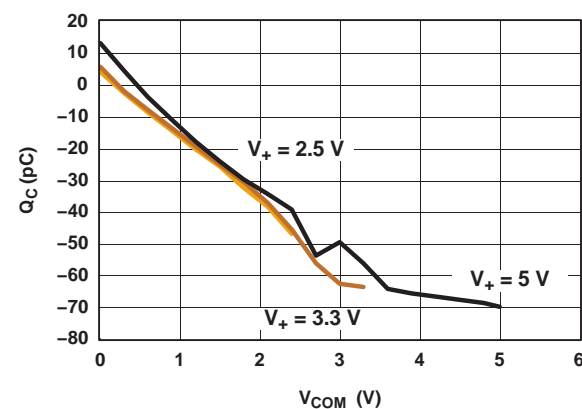


**ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY<sup>(1)</sup> (continued)**
 $V_+ = 2.25\text{ V to }2.75\text{ V}$ ,  $V_{IO} = 1.65\text{ V to }1.95\text{ V}$ ,  $T_A = -40^\circ\text{C to }85^\circ\text{C}$  (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T <sub>A</sub>	V+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t <sub>ON</sub>	V <sub>COM</sub> = V <sub>+</sub> , R <sub>L</sub> = 50 Ω,	C <sub>L</sub> = 35 pF, See <a href="#">Figure 18</a>	25°C	2.5 V	5	20	35	ns
				Full	2.25 V	5		40	
Turn-off time	t <sub>OFF</sub>	V <sub>COM</sub> = V <sub>+</sub> , R <sub>L</sub> = 50 Ω,	C <sub>L</sub> = 35 pF, See <a href="#">Figure 18</a>	25°C	2.5 V	2	10	20	ns
				Full	2.25 V	2		25	
Break-before-make time	t <sub>BBM</sub>	V <sub>NC</sub> = V <sub>NO</sub> = V <sub>+</sub> /2, R <sub>L</sub> = 50 Ω,	C <sub>L</sub> = 35 pF, See <a href="#">Figure 19</a>	25°C	2.5 V	1	11	20	ns
				Full	2.25 V	1		25	
Charge injection	Q <sub>C</sub>	V <sub>GEN</sub> = 0, R <sub>GEN</sub> = 0,	C <sub>L</sub> = 1 nF, See <a href="#">Figure 23</a>	25°C	2.5 V		5		pC
NO OFF capacitance	C <sub>NO(OFF)</sub>	V <sub>NO</sub> = V <sub>+</sub> or GND, Switch OFF,	See <a href="#">Figure 17</a>	25°C	2.5 V		38		pF
NC, NO ON capacitance	C <sub>NC(ON)</sub> , C <sub>NO(ON)</sub>	V <sub>NC</sub> or V <sub>NO</sub> = V <sub>+</sub> or GND, Switch ON,	See <a href="#">Figure 17</a>	25°C	2.5 V		135		pF
COM ON capacitance	C <sub>COM(ON)</sub>	V <sub>COM</sub> = V <sub>+</sub> or GND, Switch ON,	See <a href="#">Figure 17</a>	25°C	2.5 V		135		pF
Digital input capacitance	C <sub>I</sub>	V <sub>I</sub> = V <sub>IO</sub> or GND,	See <a href="#">Figure 17</a>	25°C	2.5 V		6.5		pF
Bandwidth	BW	R <sub>L</sub> = 50 Ω, Switch ON,	See <a href="#">Figure 20</a>	25°C	2.5 V		40		MHz
OFF isolation	O <sub>ISO</sub>	R <sub>L</sub> = 50 Ω, f = 1 MHz,	See <a href="#">Figure 21</a>	25°C	2.5 V		−63		dB
Crosstalk	X <sub>TALK</sub>	R <sub>L</sub> = 50 Ω, f = 1 MHz,	See <a href="#">Figure 22</a>	25°C	2.5 V		−63		dB
Total harmonic distortion	THD	R <sub>L</sub> = 600 Ω, C <sub>L</sub> = 50 pF,	f = 20 Hz to 20 kHz, See <a href="#">Figure 24</a>	25°C	2.5 V		0.008		%
Supply									
Positive supply current	I <sub>+</sub>	V <sub>I</sub> = V <sub>IO</sub> or GND		25°C	2.75 V		10	25	nA
				Full				100	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

## TYPICAL PERFORMANCE

Figure 1.  $r_{on}$  vs  $V_{COM}$  ( $V_+ = 2.5$  V)Figure 2.  $r_{on}$  vs  $V_{COM}$  ( $V_+ = 3.3$  V)Figure 3.  $r_{on}$  vs  $V_{COM}$  ( $V_+ = 5$  V)Figure 4. Leakage Current vs Temperature ( $V_+ = 5$  V)Figure 5.  $I_+$  vs Temperature ( $V_+ = 5$  V)Figure 6. Charge Injection ( $Q_C$ ) vs  $V_{COM}$

## TYPICAL PERFORMANCE (continued)

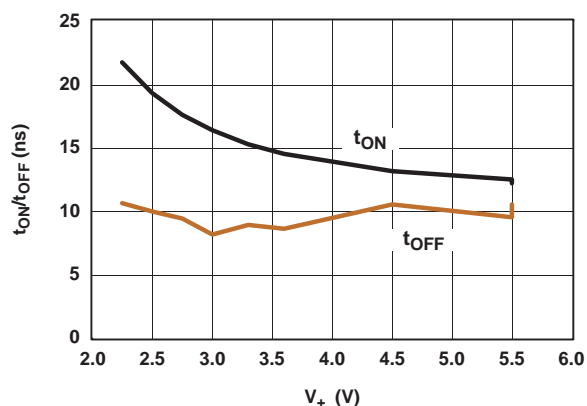


Figure 7.  $t_{ON}/t_{OFF}$  vs Supply Voltage

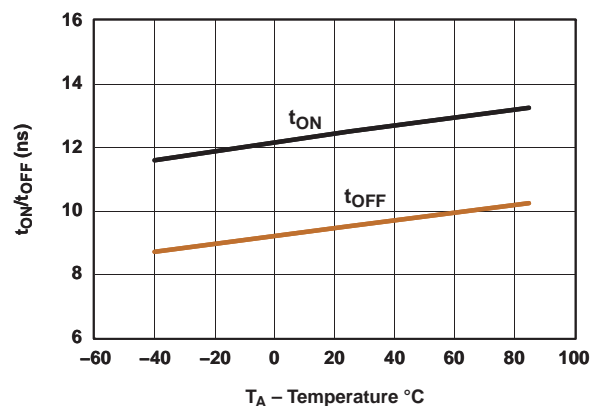


Figure 8.  $t_{ON}/t_{OFF}$  vs Temperature ( $V_+ = 5$  V)

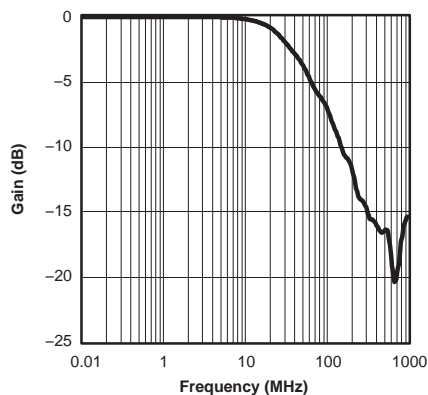


Figure 9. Gain vs Frequency ( $V_+ = 5$  V)

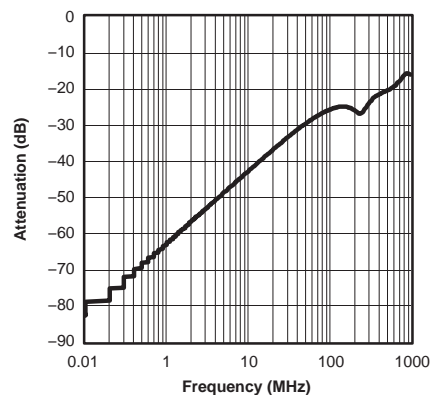


Figure 10. Crosstalk vs Frequency ( $V_+ = 5$  V)

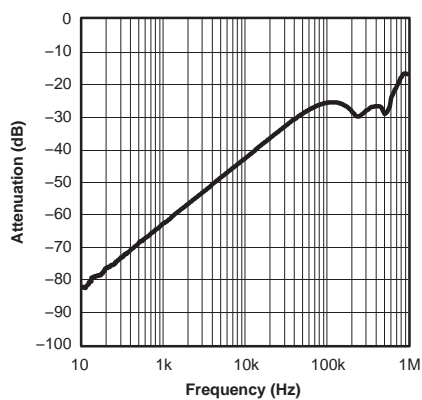


Figure 11. OFF Isolation vs Frequency ( $V_+ = 5$  V)

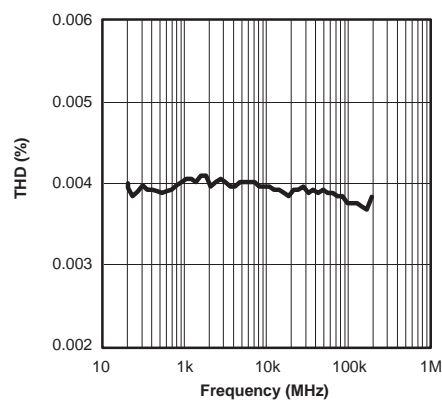
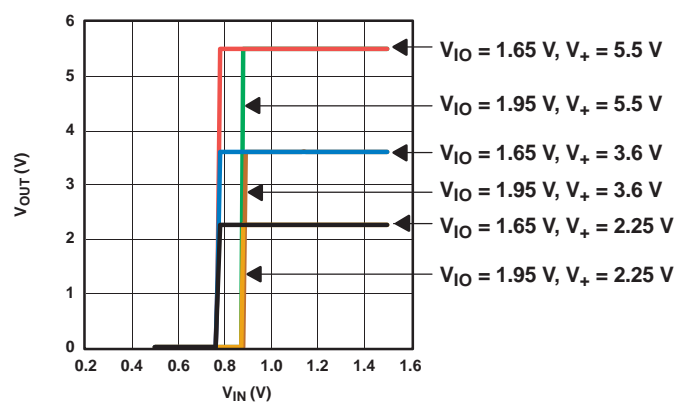
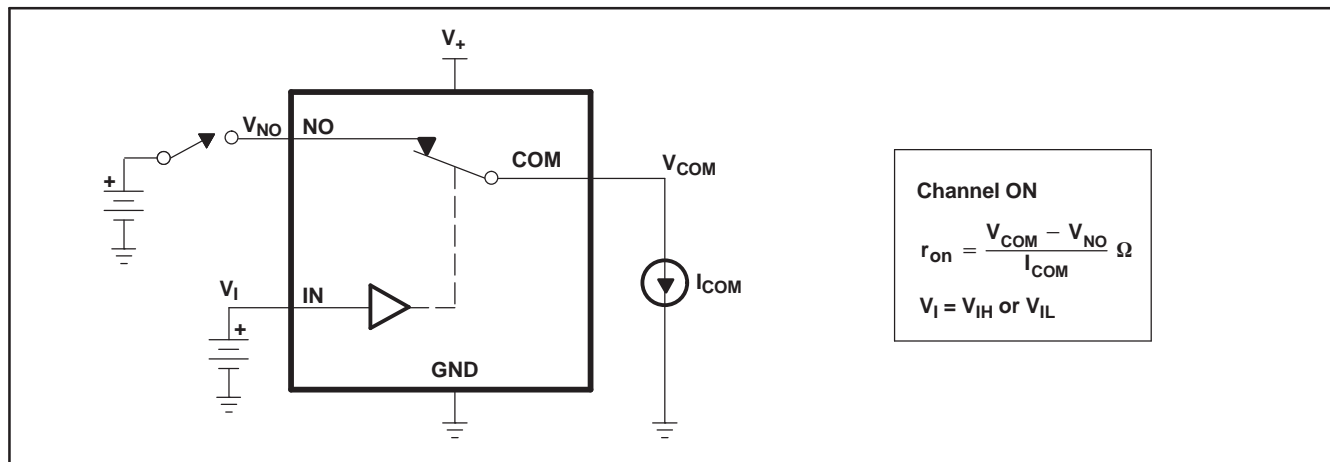


Figure 12. Total Harmonic Distortion vs Frequency ( $V_+ = 2.5$  V)

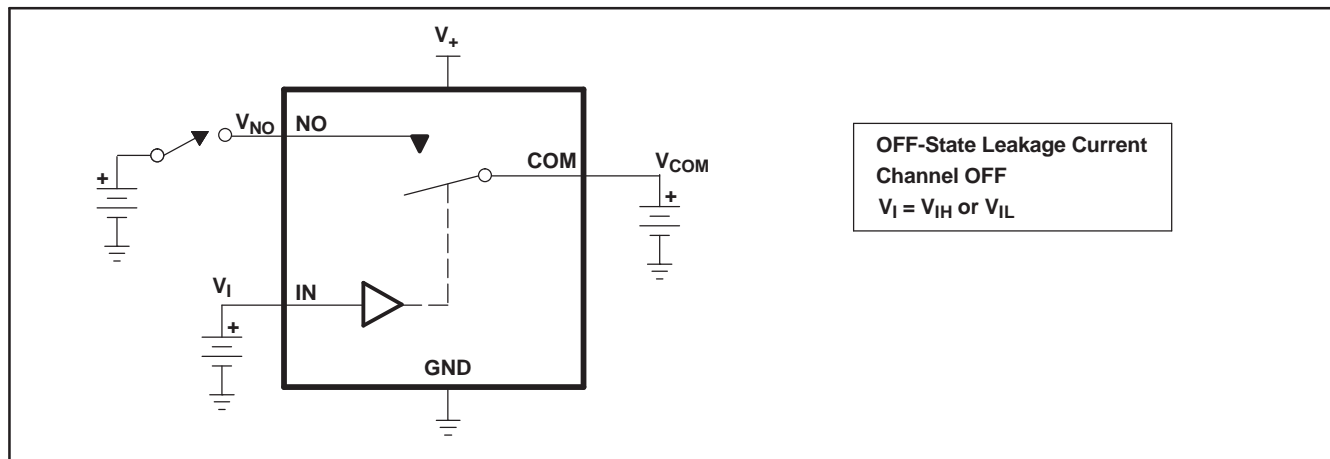
## TYPICAL PERFORMANCE (continued)

Figure 13.  $V_{IO}$  Thresholds

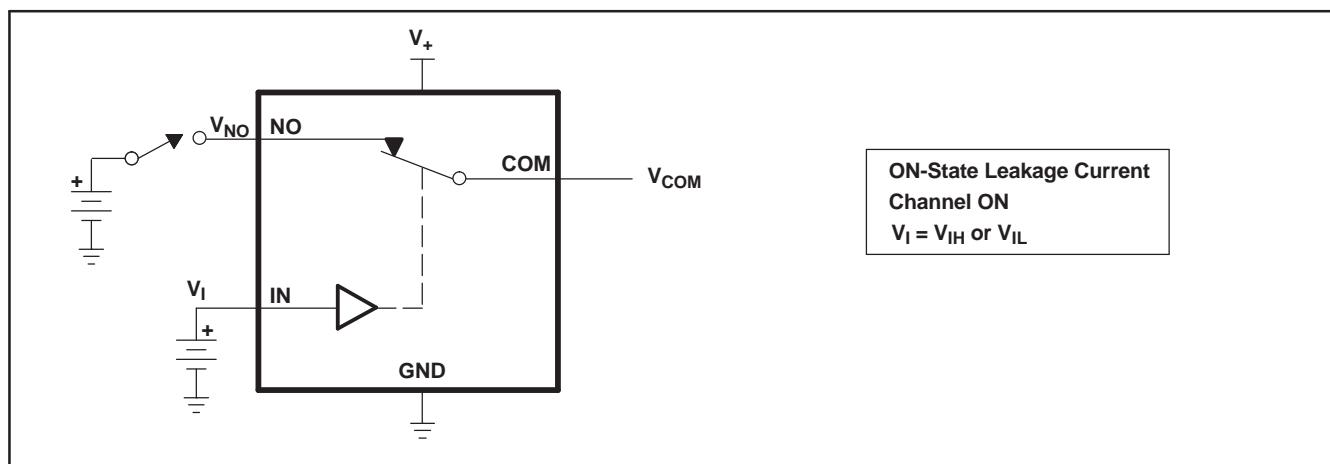
## PARAMETER MEASUREMENT INFORMATION



**Figure 14. ON-State Resistance ( $r_{on}$ )**



**Figure 15. OFF-State Leakage Current ( $I_{COM(OFF)}$ ,  $I_{NC(OFF)}$ ,  $I_{COM(PWROFF)}$ ,  $I_{NC(PWRFF)}$ )**



**Figure 16. ON-State Leakage Current ( $I_{COM(ON)}$ ,  $I_{NC(ON)}$ )**

## PARAMETER MEASUREMENT INFORMATION (continued)

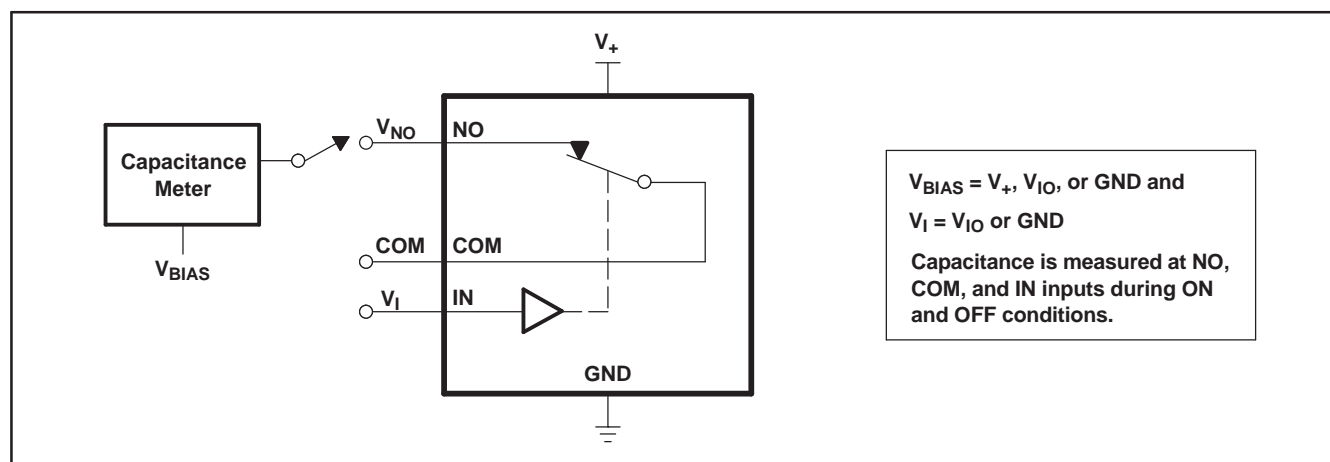
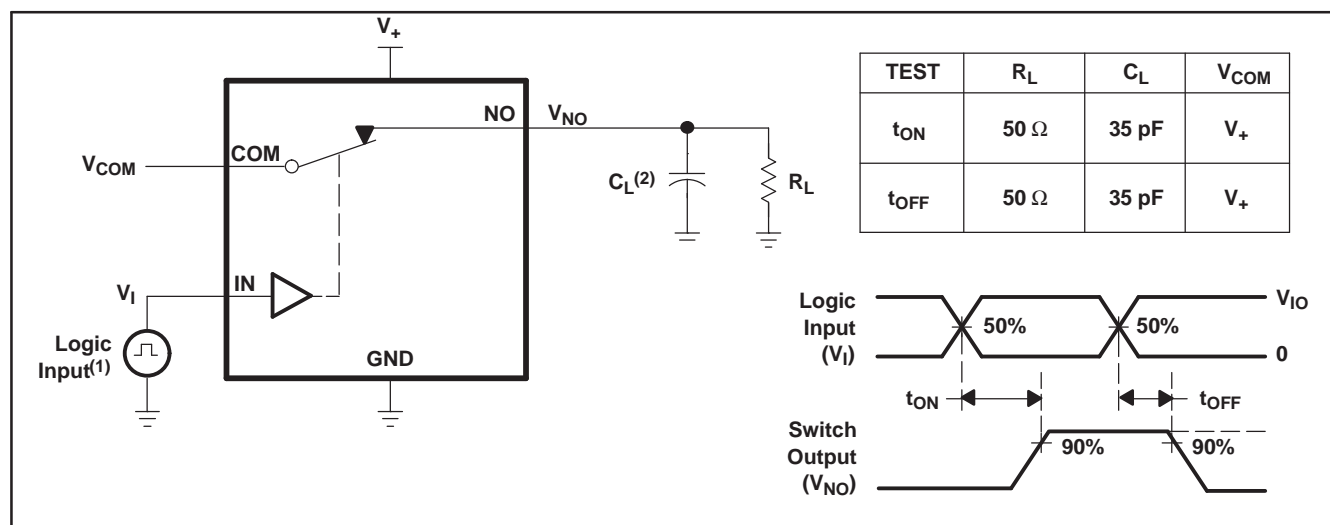


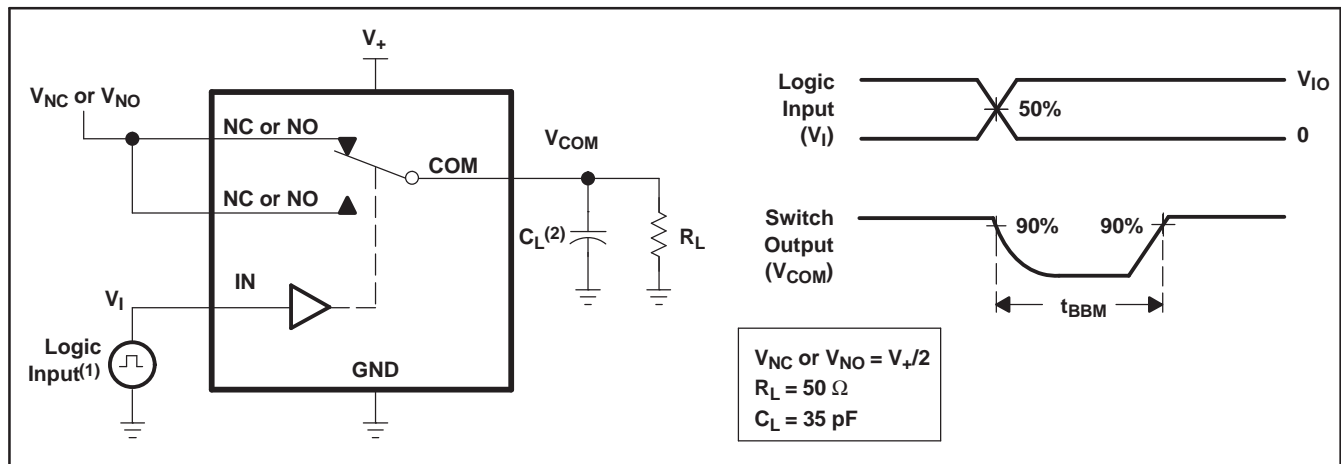
Figure 17. Capacitance ( $C_I$ ,  $C_{COM(OFF)}$ ,  $C_{COM(ON)}$ ,  $C_{NC(OFF)}$ ,  $C_{NC(ON)}$ )



NOTES: A. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10\ \text{MHz}$ ,  $Z_O = 50\ \Omega$ ,  $t_r < 5\ \text{ns}$ ,  $t_f < 5\ \text{ns}$ .  
 B.  $C_L$  includes probe and jig capacitance.

Figure 18. Turn-On ( $t_{ON}$ ) and Turn-Off Time ( $t_{OFF}$ )

## PARAMETER MEASUREMENT INFORMATION (continued)



NOTES: A. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10 \text{ MHz}$ ,  $Z_O = 50 \Omega$ ,  $t_r < 5 \text{ ns}$ ,  $t_f < 5 \text{ ns}$ .  
B.  $C_L$  includes probe and jig capacitance.

Figure 19. Break-Before-Make Time ( $t_{BBM}$ )

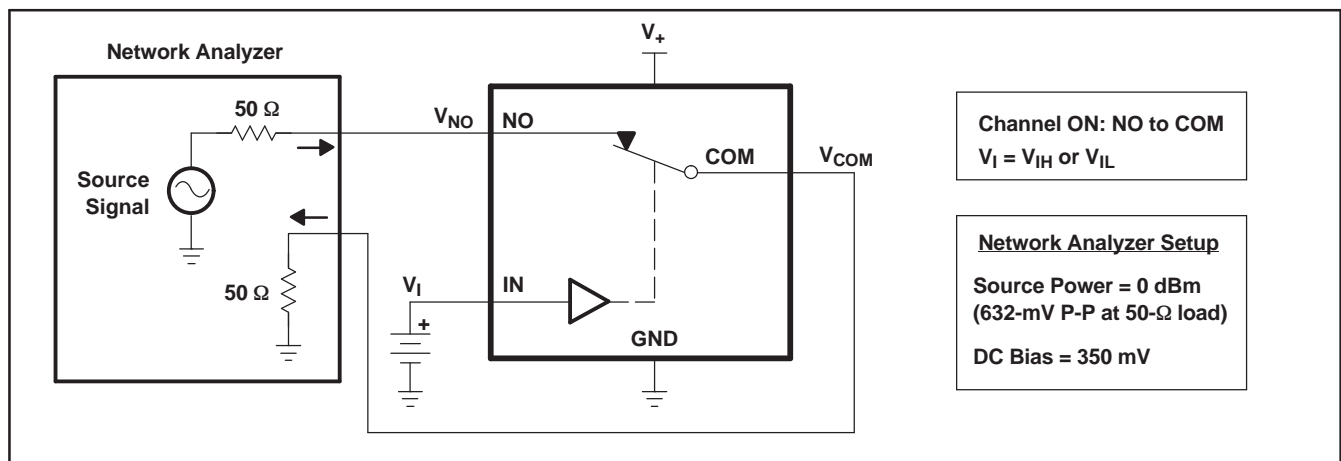


Figure 20. Bandwidth (BW)

## PARAMETER MEASUREMENT INFORMATION (continued)

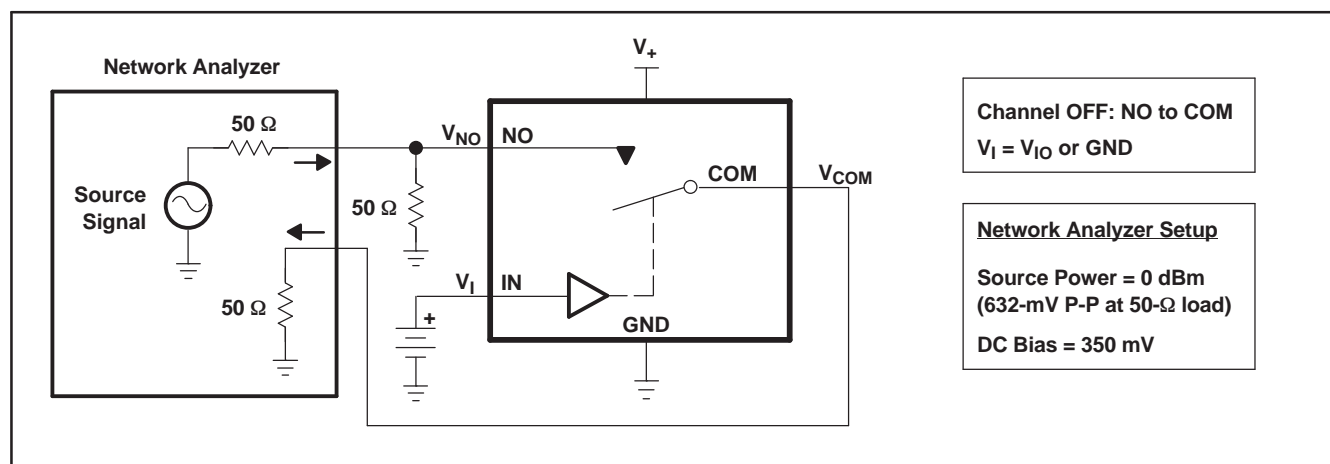


Figure 21. OFF Isolation ( $O_{ISO}$ )

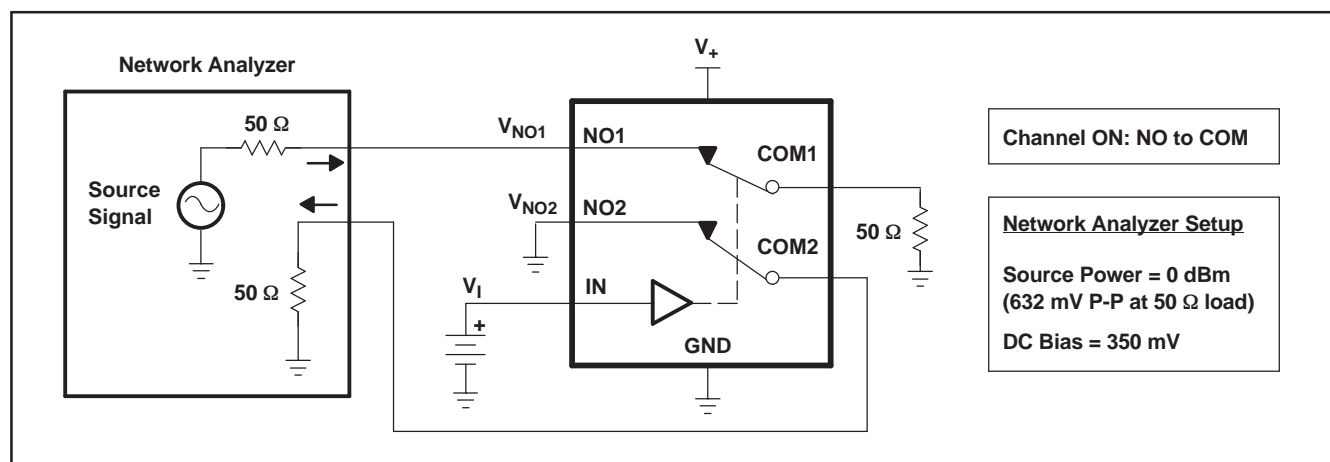
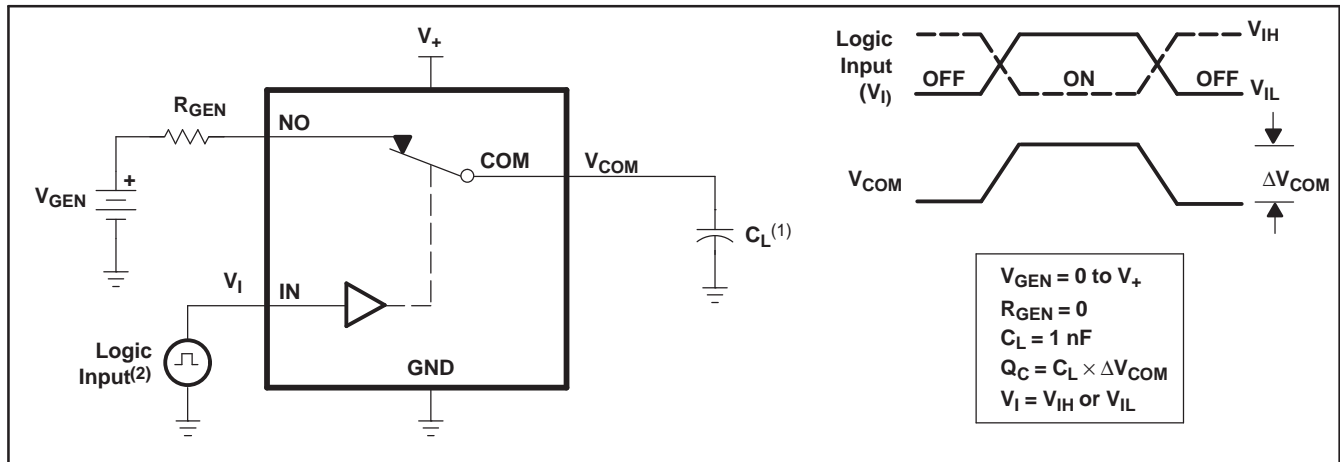


Figure 22. Crosstalk ( $X_{TALK}$ )

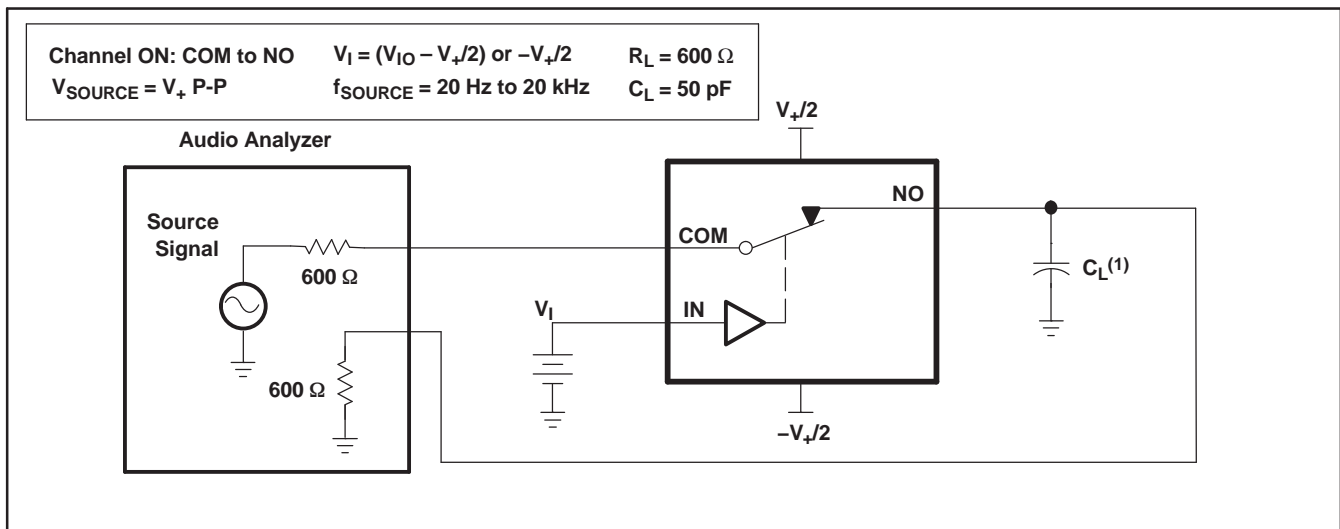


## PARAMETER MEASUREMENT INFORMATION (continued)



NOTES: A.  $C_L$  includes probe and jig capacitance.  
B. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10$  MHz,  $Z_O = 50 \Omega$ ,  $t_r < 5$  ns,  $t_f < 5$  ns.

Figure 23. Charge Injection ( $Q_C$ )



NOTES: A.  $C_L$  includes probe and jig capacitance.

Figure 24. Total Harmonic Distortion (THD)

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TS5A26542YZTR	ACTIVE	DSBGA	YZT	12	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(JN2, JN7, JNN)	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A26542YZTR	DSBGA	YZT	12	3000	178.0	9.2	1.49	1.99	0.75	4.0	8.0	Q2

## TAPE AND REEL BOX DIMENSIONS



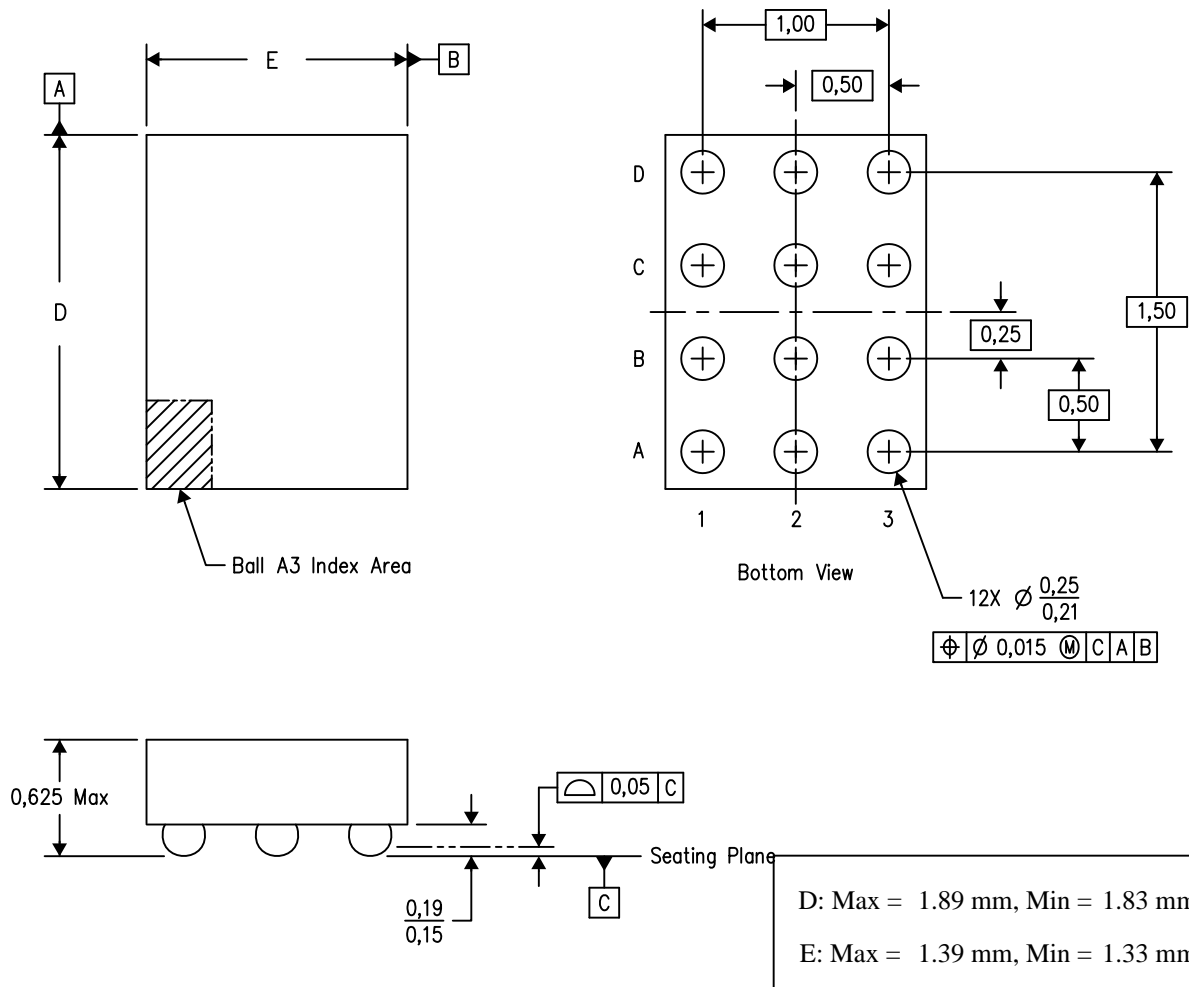
\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A26542YZTR	DSBGA	YZT	12	3000	220.0	220.0	35.0

## MECHANICAL DATA

YZT (R-XBGA-N12)

(CUSTOM) DIE-SIZE BALL GRID ARRAY



4205418-6/H 05/13

- NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.  
B. This drawing is subject to change without notice.  
C. NanoFree™ package configuration.

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